

Product Discontinuation Notices

December 1, 2009

Photomicro Sensors

No. 2009303E

Discontinuation Notice of Photomicrosensors. EE-SB5M series

Product Discontinuation



EE-SB5M Series

Recommended Replacement



Please contact the appropriate division
EE-SY672
(except the EE-SB5M-F and EE-SB5M-G)

Discontinuation date : The end of May, 2010

Caution on recommended replacement

Our Amplified photomicrosensors, model EE-SB5M series will be discontinued at the end of May, 2010. We recommend Amplified photomicrosensors, type EE-SY672 for replacement of them (except the EE-SB5M-F, EE-SB5M-G and EE-SB5MC-H). And we recommend to change your products design or to order it collectively including a necessary amount in the future by May, 2010.

Difference from discontinued product

Model	Body Color	Dimensions	Wire connection	Mounting Dimensions	Characteristics	Operation ratings	Operation methods
EE-SY672	**	*	*	*	*	*	**

** : Fully compatible

* : The change is a little/Almost compatible

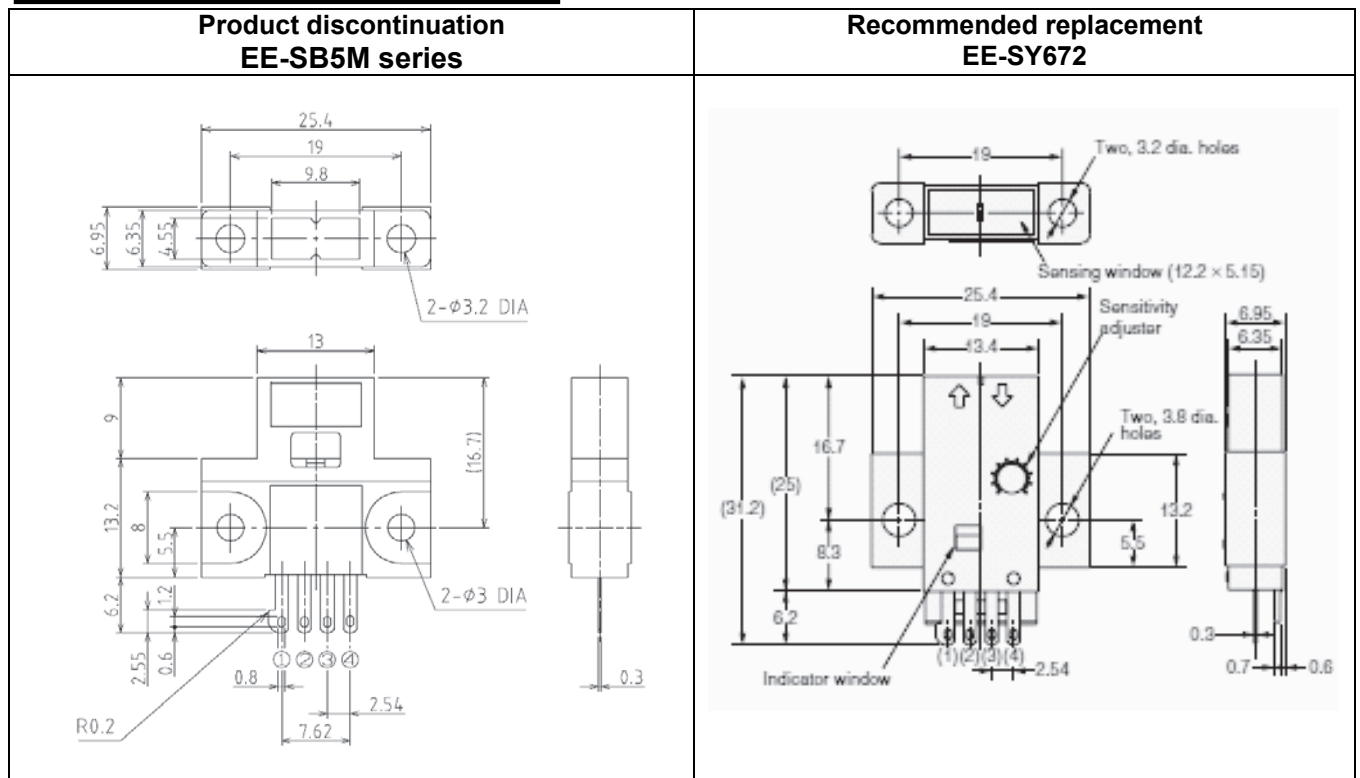
-- : Not compatible

- : No corresponding specification

Product Discontinuation and recommended replacement

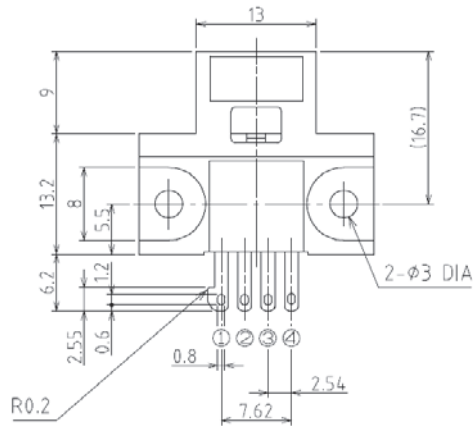
Product discontinuation		Recommended replacement	
Model	Product code	Model	Product code
EE-SB5M	EESB1001H	EE-SY672	EESY1124M
EE-SB5M-F	EESB2030G	No recommended replacement	
EE-SB5M-G	EESB2031E	No recommended replacement	
EE-SB5MC	EESB2001C	EE-SY672	EESY1124M
EE-SB5MC-H	EESB2011M	No recommended replacement	

Dimensions



Terminal dimension

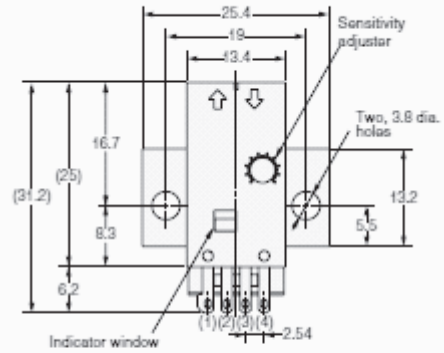
Product discontinuation EE-SB5M series



Terminal Arrangement

1	+	Vcc
2	L	L
3	OUT	OUTPUT
4	-	GND(0V)

Recommended replacement EE-SY672

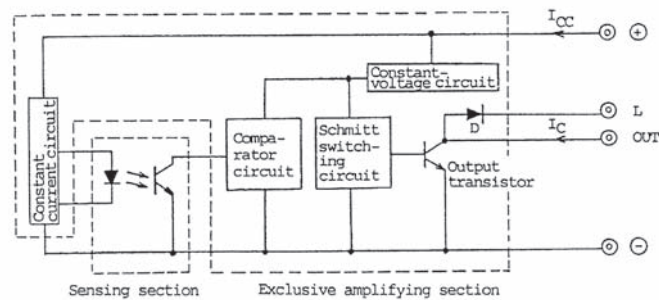


Terminal Arrangement

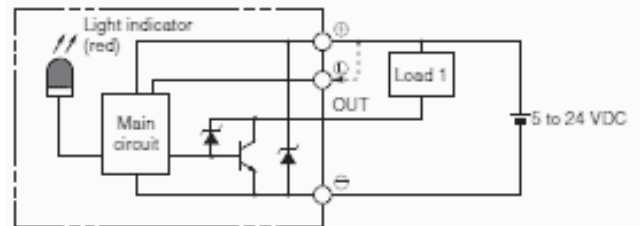
(1)	-	Vcc
(2)	L	L
(3)	OUT	OUTPUT
(4)	-	GND (0 V)

Internal connection

Product discontinuation EE-SB5M series



Recommended replacement EE-SY672



Characteristics

Item		Product discontinuation		Recommended replacement	
		EE-SB5M	EE-SB5MC	EE-SY672	
Sensing distance		5mm (Reflection factor 90%)		1 to 5mm (Reflection factor 90%)	
Differential distance		0.1mm		0.5mm	
Light source		GaAs infrared LED		GaAs infrared LED	
Supply voltage		5-10% to 12+10% VDC Ripple (p-p): 10% MAX.		5-10% to 24+10% VDC Ripple (p-p): 10% MAX.	
Current consumption		36mA MAX.		40mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 80mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.		Load power supply voltage: 5 to 24VDC 100mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.	
Stage of output transistor	Stage of output transistor when object is not sensed	OFF	ON	OFF (Terminal [L] is short-circuited)	ON (Terminal [L] is opened)
	Stage of output transistor when object is sensed	ON	OFF	ON (Terminal [L] is short-circuited)	OFF (Terminal [L] is opened)
Response frequency		50Hz		50Hz	
Ambient temperature range		Operating : -25 to +55°C Storage : -30 to +80°C		Operating : -25 to +55°C Storage : -30 to +80°C	
Ambient humidity range		Operating : 5 to 85%RH Storage : 5 to 95%RH		Operating : 5 to 85%RH Storage : 5 to 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions		Destruction: 20 to 2000 Hz (Peak acceleration: 100m/s ²) 1.5mm double amplitude for 2h (4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions		Destruction: 500m/S ² for 3 times each in X, Y and Z directions	

Characteristics

Item		Product discontinuation EE-SB5M-F	Recommended replacement No type
Sensing distance		9.4mm (Reflection factor 18%)	
Differential distance		0.1mm	
Light source		GaAs infrared LED	
Supply voltage		5-10% to 12+10% VDC Ripple (p-p): 10% MAX.	
Current consumption		36mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 80mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.	
Stage of output transistor	Stage of output transistor when object is not sensed	OFF	
	Stage of output transistor when object is sensed	ON	
Response frequency		50Hz	
Ambient temperature range		Operating : -25 to +55°C Storage : -30 to +80°C	
Ambient humidity range		Operating : 5 to 85%RH Storage : 5 to 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions	

Characteristics

Item		Product discontinuation EE-SB5M-G	Recommended replacement No type
Sensing distance		11.4mm (Reflection factor 90% : white paper)	
Differential distance		0.1mm	
Light source		GaAs infrared LED	
Supply voltage		5-10% to 12+10% VDC Ripple (p-p): 10% MAX.	
Current consumption		36mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 10mA load current with a residual voltage 0.4V MAX.	
Stage of output transistor	Stage of output transistor when object is not sensed	OFF	
	Stage of output transistor when object is sensed	ON	
Response frequency		50Hz	
Ambient temperature range		Operating : -25 to +55°C Storage : -30 to +80°C	
Ambient humidity range		Operating : 45 to 85%RH Storage : 35 to 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions	

Characteristics

Item		Product discontinuation EE-SB5MC-H	Recommended replacement No type
Sensing distance		5 to 15mm (Reflection factor 90%)	
Differential distance		0.1mm	
Light source		GaAs infrared LED	
Supply voltage		5-10% to 12+10% VDC Ripple (p-p): 10% MAX.	
Current consumption		36mA MAX.	
Control output		Load power supply voltage: 5 to 24VDC 80mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.	
Stage of output transistor	Stage of output transistor when object is not sensed	ON	
	Stage of output transistor when object is sensed	OFF	
Response frequency		50Hz	
Ambient temperature range		Operating : -25 to +55°C Storage : -30 to +80°C	
Ambient humidity range		Operating : 10 to 85%RH Storage : 10 to 95%RH	
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions	
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions	